|  |                |  |   |   |                    | <u>SHEET 1 OF 1</u>   |  |
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| INFORMATION DISCLOSURE CITATION IN ANOTE APPLICATION |                |  |   | ATTY. DOCKET NO. 63979-028                                |                    | RIAL NO.<br>616,917   |  |
| DEC 1 0 2003   |                |  |   | APPLICANT Takashi NISHIKAWA, et al.                       |                    |   |  |
| (PTO-1449) 2 CRADENARY OF                            |                |  |   | FILING DATE July 11, 2003                                 | GROUP 2811         |   |  |
| U.S. PATENT DOCUMENTS                                |                |  |   |   |                    |   |  |
| EXAMINER'S<br>INITIALS                               | CITE<br>NO.    | Document Number Number-Kind Code2 (7 known)  | Publication Date<br>MM-DD-YYYY                                | Name of Patentee or Applia<br>Document                    | cant of Cited      | Pages, Columns, Lines, Where<br>Relevant Passages or Relevant<br>Figures Appear   |  |
|  | <del></del>    | US 2001/0028582 A1   | 10/11/2001  | Tarui et al-  | <del></del>        |   |  |
| <u> </u>   |                | US 6,407,435 B1  | 06/18/2002  | Ma et al.   |                    |   |  |
|  |                | US   |   |   |                    |   |  |
|  |                | US   | ]   | /   |                    |   |  |
|  |                | US   |   |   |                    |   |  |
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| EXAMINER'S<br>INITIALS                               | CITE<br>NO.    | Foreign Patent Document<br>Country Codes -Number 4 -Kind<br>Codes (if known)   | Publication Date M of Patentee or Applicant of Cited Document | Pages, Columns, Lines<br>Where Relevant Figures<br>Appear | T14ranslation      |   |  |
|  |                |  | ;   |   |                    | Yes N   |  |
| 11.01  | Z <sub>A</sub> | JP 08-204404   | 07/22/1994  | HITACHI LTD   |                    | Japanese (w/ English  |  |
| upuca  | te.            |  |   |   |                    | Abstract)   |  |
| 'KR  |                | JP 11-1680 <u>69</u>   | 06/22/1999  | SONY CORP   |                    | Japanese (w/PartialEnglish<br>Translation & Abstract)   |  |
| uplicate   | A              | JP:P2002 313966  | 10/25/2002  | NIPPON PRECISION CIRCUITS INC                             |                    | depanese (w/ English<br>Abstract)   |  |
| 11 NICAF   | <del></del>    | < <u>EP-1124262</u>  | 08/16/2001  | SHARP KABUSHIKI KAISHA                                    |                    | radiou)   |  |
| munu   |                | <u> </u>   |   |   | **                 |   |  |
| 到2000年/最大  | 47 70          | SCHOTHER!  | RT/(including/Author)   | Title: Date Pertinent Pages Et                            | C) * S   No   SE   |   |  |
| EXAMINER'S<br>INITIALS                               | CITE<br>NO.    | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where                   |   |   |                    |   |  |
|  |                | Mitsue Takahashi et al., "ANALYSIS AND IMPROVEMENT OF RETENTION TIME OF MEMORIZED STATE OF METAL-<br>FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE FOR FERROELECTRIC GATE FET MEMORY: This<br>Japan Society of Applied Physics, January 5, 2001, pp. 2923-2927 |   |   |                    |   |  |
|  |                |  |   |   |                    |   |  |
|  |                | upucace  |   |   |                    |   |  |
|  | LK             |  |   | -   |                    |   |  |
| H  | : K191         | EXAMINER<br>Q  |   | Sept. 22, 2007  |                    |   |  |
| EXAMINER: Initial of Include copy of this for        | reference      | considered, whether or not citatext communication to applicant.  | ion is in conformance   | with MPEP 609. Draw line throu                            | igh citation if no | it in conformance and not considered.   |  |

